TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

TPC8012-H

Switching Regulator Application

DC-DC Converters

- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 0.28 Ω (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 1.35 S (typ.)
- Low leakage current: I_{DSS} = 100 μA (max) (V_{DS} = 200 V)
- Enhancement mode: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 1 mA)

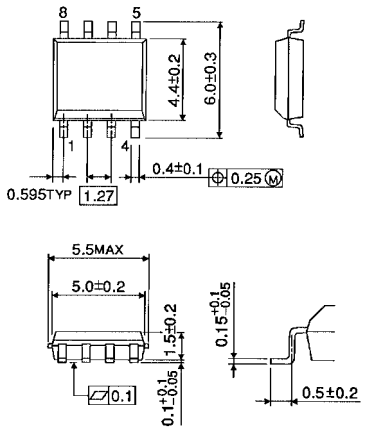
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	200	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	200	V
Gate-source voltage		V_{GSS}	±30	V
Drain current	DC (Note 1)	I_D	1.8	A
	Pulse (Note 1)	I_{DP}	7.2	
Drain power dissipation (t = 10 s) (Note 2a)		P_D	1.9	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	1.0	W
Single pulse avalanche energy (Note 3)		E_{AS}	2.05	mJ
Avalanche current		I_{AR}	1.8	A
Repetitive avalanche energy (Note 2a) (Note 4)		E_{AR}	0.19	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Note: (Note 1), (Note 2), (Note 3), (Note 4) Please see next page.

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm

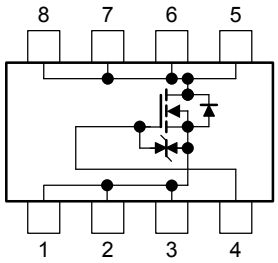


1, 2, 3 SOURCE
4 GATE
5, 6, 7, 8 DRAIN

JEDEC	TO-92
JEITA	—
TOSHIBA	2-6J1B

Weight: 0.80 g (typ.)

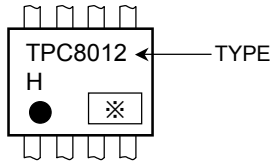
Circuit Configuration



Thermal Characteristics

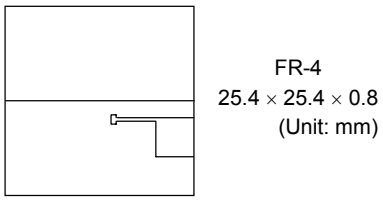
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch\text{-}a)}$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch\text{-}a)}$	125	°C/W

Marking (Note 5)

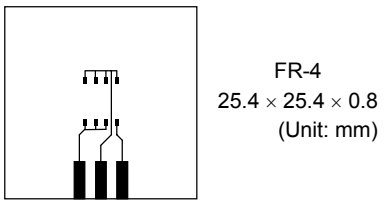


Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



(a)



(b)

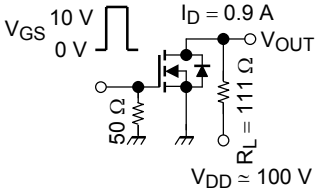
Note 3: V_{DD} = 50 V, T_{ch} = 25°C (initial), L = 1.0 mH, R_G = 25 Ω, I_{AR} = 1.8 A

Note 4: Repetitive rating; pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1.

※ shows lot number. (year of manufacture: last decimal digit of the year of manufacture, month of manufacture: January to December are denoted by letters A to L respectively.)

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±25 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut-OFF current		I_{DSS}	V_{DS} = 200 V, V_{GS} = 0 V	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	200	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	3.0	—	5.0	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 10 V, I_D = 0.9 A	—	0.28	0.40	Ω
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 0.9 A	0.65	1.35	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	440	—	pF
Reverse transfer capacitance		C_{rss}		—	80	—	
Output capacitance		C_{oss}		—	260	—	
Switching time	Rise time	t_r	 Duty ≦ 1%, t_w = 10 μs	—	23	—	ns
	Turn-ON time	t_{on}		—	28	—	
	Fall time	t_f		—	22	—	
	Turn-OFF time	t_{off}		—	73	—	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≃ 160 V, V_{GS} = 10 V, I_D = 1.8 A	—	11	—	nC
Gate-source charge 1		Q_{gs1}		—	6	—	
Gate-drain (“miller”) charge		Q_{gd}		—	5	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	7.2	A
Forward voltage (diode)		V_{DSF}	I_{DR} = 1.8 A, V_{GS} = 0 V	—	—	−1.5	V

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